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hot carriers into the gate insulation film is restrained.

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SOLUTION: In the superjunction semiconductor device, provided with a drain/drift section 22 of a parallel p-n structure, in the parts of a p-type partition regions 22b which are under wells of p-type base regions 13, p-type withstand voltage limiter regions 30 having a high impurity concentration are formed. In off-state, the voltage reaches the critical voltage earlier in the central part of the withstand voltage limiter regions 30 than that at an E point directly below a gate insulation film. As a result, a surface electric field is reduced at the E point, and injection of

